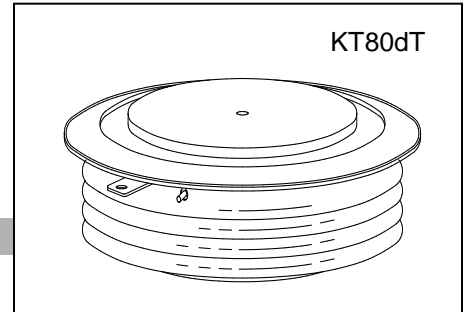




FREE FLOATING TYPE THYRISTOR FOR PHASE CONTROL APPLICATIONS

Features:

- . Free-floating silicon technology
- . Low on-state and switching losses
- . Optimum power handling capability
- . Blocking capability up to 7200 volts
- . Distributed amplifying gate



ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V <sub>RRM</sub> (1)	V <sub>DRM</sub> (1)	V <sub>RSM</sub> (1)
KP1150/68	6800	6800	6800
KP1150/70	7000	7000	7000
KP1150/72	7200	7200	7200

V<sub>RRM</sub> = Repetitive peak reverse voltage  
V<sub>DRM</sub> = Repetitive peak off state voltage  
V<sub>RSM</sub> = Non repetitive peak reverse voltage (2)

Notes:

- (1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range 0 to +115 °C.
- (2) 10 msec. max. pulse width
- (3) Maximum value for T<sub>j</sub> = 115 °C.
- (4) Minimum value for linear and exponential waveshape to 67% rated V<sub>DRM</sub>. Gate open. T<sub>j</sub> = 115 °C.
- (5). The value of di/dt is established in accordance with JBT/ 8950.2-2013

Repetitive peak reverse leakage and off state leakage	I <sub>RRM</sub> /I <sub>DRM</sub>	10mA 100 mA (3)
Critical rate of voltage rise	dv/dt (4)	2000 V/sec (min)

Conducting - On State

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average value of on-state current	I <sub>T(AV)</sub>		1150		A	Sinewave, 180° conduction, T <sub>c</sub> =70°C
RMS value of on-state current	I <sub>TRMS</sub>		1805		A	Nominal value
Peak one cycle surge (non repetitive) current	I <sub>TSM</sub>		18300		A	10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, T <sub>j</sub> = 115 °C
I square t	I <sup>2</sup> t		1.6x10 <sup>6</sup>		A <sup>2</sup> s	10 msec
Latching current	I <sub>L</sub>		1000		mA	V <sub>D</sub> = 12 V; R <sub>L</sub> = 12 ohms
Holding current	I <sub>H</sub>		200		mA	V <sub>D</sub> = 12 V; I = 2.5 A
Peak on-state voltage	V <sub>TM</sub>		2.40		V	I <sub>TM</sub> =1500A; T <sub>j</sub> =25°C
Threshold voltage, low-level	V <sub>TO</sub>		1.25		V	T <sub>j</sub> =115°C
Slope resistance, low-level	r <sub>T</sub>		0.76		mΩ	1000A to 3000A
Critical rate of rise of on-state current	di/dt		100		A/μs	Repetition

### Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P <sub>GM</sub>		20		W	
Average gate power dissipation	P <sub>G(AV)</sub>		4		W	
Gate-trigger current	I <sub>GT</sub>		300		mA	V <sub>D</sub> =12 V;R <sub>L</sub> = 3 ohms;T <sub>j</sub> = +25 °C
Gate- trigger voltage	V <sub>GT</sub>	0.8	3.0		V	V <sub>D</sub> = 12 V;R <sub>L</sub> = 3 ohms;T <sub>j</sub> = +25 °C
Peak negative voltage	V <sub>GRM</sub>		10		V	

### Dynamic

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	t <sub>d</sub>		3.0		μs	I <sub>FG</sub> =2.0A; V <sub>D</sub> =0.4V <sub>DRM</sub> ; t <sub>r</sub> =0.5μs
Turn-off time (with V <sub>R</sub> = -5 V)	t <sub>q</sub>		800		μs	I <sub>TM</sub> =1000 A; di/dt =- 10A/μs; V <sub>R</sub> =100 V; dV/dt=30V/μs ; V <sub>D</sub> = 67%V <sub>DRM</sub> ;T <sub>j</sub> =115°C
Reverse recovery charge	Q <sub>rr</sub>		2000		μC	I <sub>TM</sub> =1000A; di/dt=-1 A/s; V <sub>R</sub> =100 V; T <sub>j</sub> =115 °C

### THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T <sub>j</sub>	-40	+115		°C	
Storage temperature	T <sub>stg</sub>	-40	+115		°C	
Thermal resistance - junction to case	R <sub>Θ(j-c)</sub>		0.01		°C/W	Double sided cooled
Thermal resistance - case to heatsink	R <sub>Θ(c-s)</sub>		0.003		°C/W	Double sided cooled
Mounting force	P			60	kN	
Weight	W			1.30	kg	

\* Mounting surfaces smooth, flat and greased

